

Technical Data
Data Sheet 688, Rev.-

SILICON SCHOTTKY RECTIFIER DIE

Very Low Forward Voltage Drop (150 °C T_J Operation)

Applications:

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V _{RWM}	-	60	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	60	A
Max. Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	860	A
Non-Repetitive Avalanche Energy	E _{AS}	T _J = 25 °C, I _{AS} = 8.0 A, L = 1.7 mH	54	mJ
Repetitive Avalanche Current	I _{AR}	I _{AS} decay linearly to 0 in 1 μs f limited by T _J max V _A =1.5V _R	8.0	A
Max. Junction Temperature	T _J	-	-65 to +150	°C
Max. Storage Temperature	T _{stg}	-	-65 to +150	°C

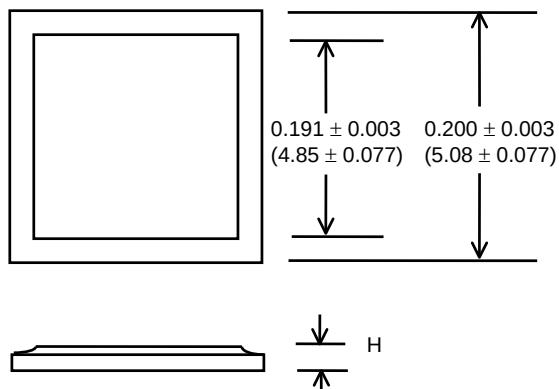
Electrical Characteristics⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 60A, Pulse, T _J = 25 °C	0.60	V
	V _{F2}	@ 60A, Pulse, T _J = 125 °C	0.57	V
Max. Reverse Current	I _{R1}	@V _R = 60V, Pulse, T _J = 25 °C	6.0	mA
	I _{R2}	@V _R = 60V, Pulse, T _J = 125 °C	420	mA
Max. Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz, V _{SIG} = 50mV (p-p)	2400	pF

(1) in SHD package

Data Sheet 688, Rev.-

Mechanical Dimensions: In Inches / mm



Bottom side metalization Ag - 30 kÅ minimum.

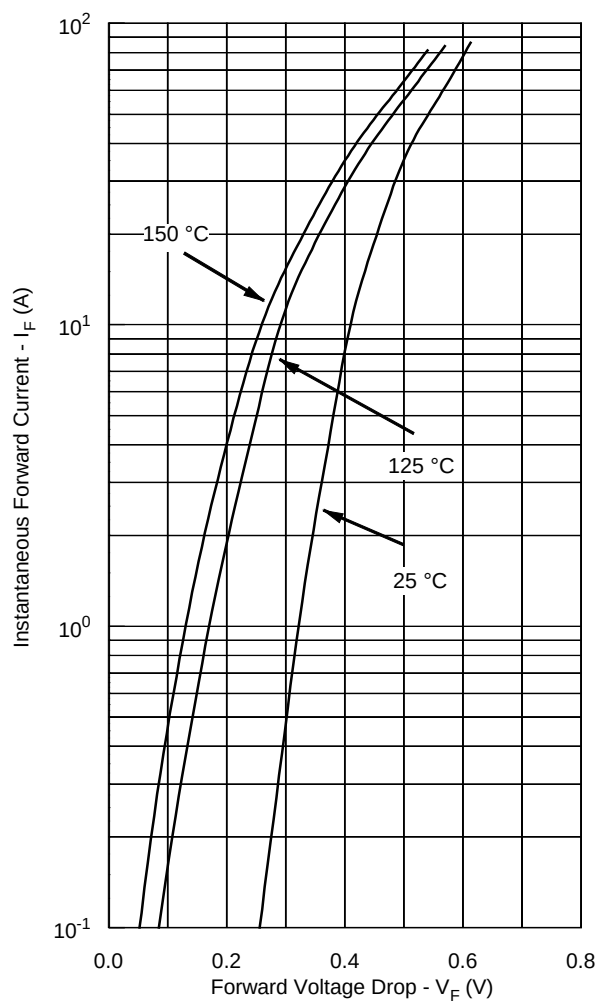
Top side metalization Al - 25 kÅ minimum
or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

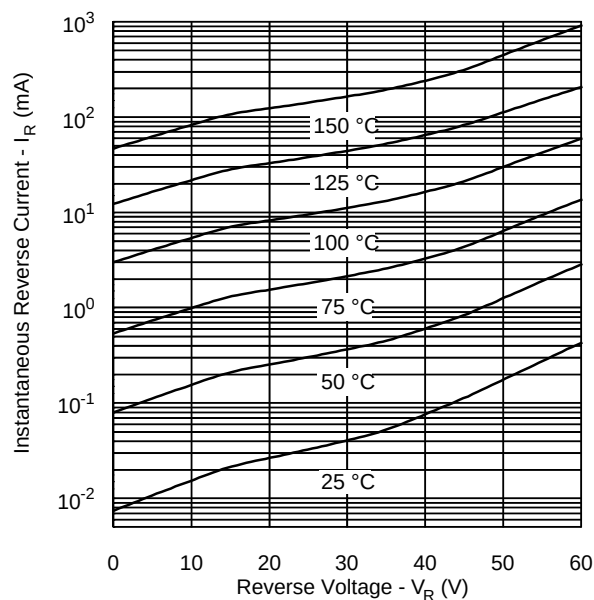
Dimension H = 0.0105 ± 0.001 (0.27 ± 0.026) for Al top;

Dimension H = 0.0155 ± 0.001 (0.39 ± 0.026) for Ag top.

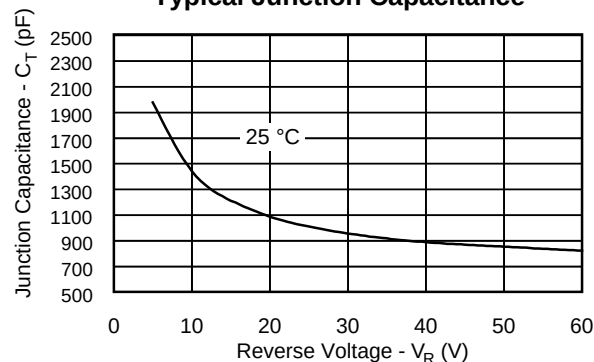
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



TECHNICAL DATA

DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the Sensitron Semiconductor sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall Sensitron Semiconductor be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). Sensitron Semiconductor assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall Sensitron Semiconductor be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or Sensitron Semiconductor.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of Sensitron Semiconductor.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.